PMZB670UPE

20 V, single P-channel Trench MOSFET Rev. 3 — 23 March 2012

Product data sheet

Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology
- ESD protection up to 2 kV
- Ultra thin package profile of 0.37 mm

1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C	<u>[1]</u>	-	-	-680	mA
Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -400 \text{ mA}; T_j = 25 \text{ °C}$		-	0.67	0.85	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



Pinning information

Table 2. **Pinning information**

	•			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source	1	D
3	D	drain	Transparent top view DFN1006B-3 (SOT883B)	G
				S 017aaa259

Ordering information

Table 3. **Ordering information**

Type number	Package		
	Name	Description	Version
PMZB670UPE	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

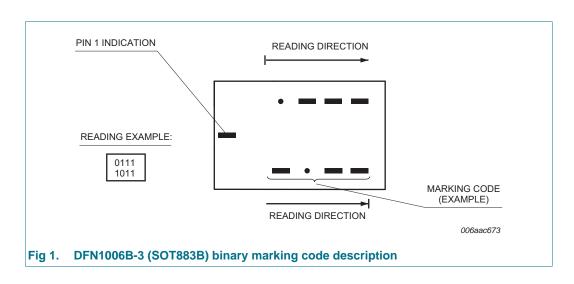
Marking

Marking codes Table 4.

Type number	Marking code ^[1]
PMZB670UPE	0000 1011

[1] For DFN1006B-3 (SOT883B) binary marking code description see Figure 1.

4.1 Binary marking code description



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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	<u>[1]</u>	-	-680	mA
		V _{GS} = -4.5 V; T _{amb} = 100 °C	<u>[1]</u>	-	-425	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	-2.7	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T _{sp} = 25 °C		-	2700	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode					
Is	source current	T _{amb} = 25 °C	<u>[1]</u>	-	-680	mA
ESD maxim	um rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

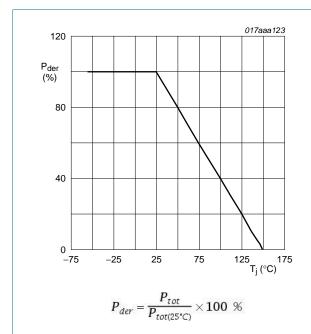
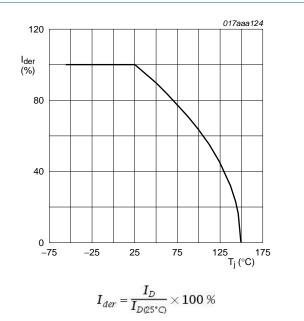
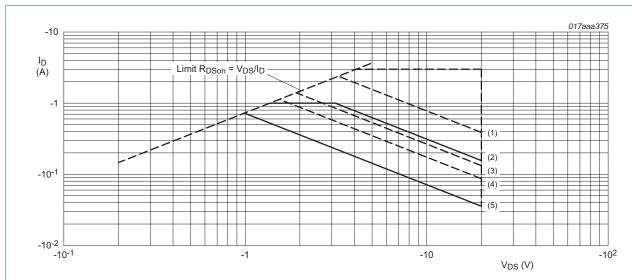


Fig 2. Normalized total power dissipation as a function of junction temperature



g 3. Normalized continuous drain current as a function of junction temperature



I_{DM} = single pulse

- (1) $t_p = 1 \text{ ms}$
- (2) DC; $T_{sp} = 25 \, ^{\circ}C$
- (3) $t_p = 10 \text{ ms}$
- (4) $t_p = 100 \text{ ms}$
- (5) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 1 cm²

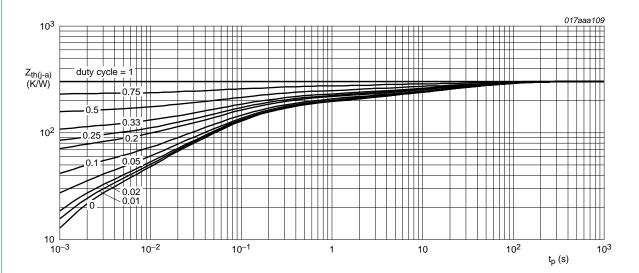
Fig 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

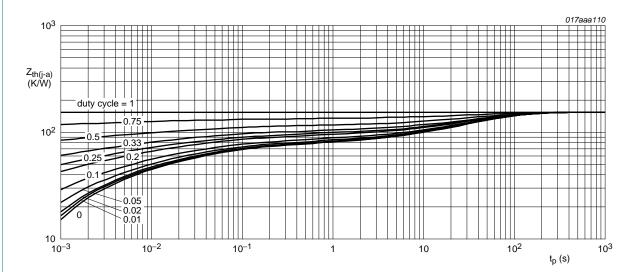
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		<u>[1]</u>	-	305	360	K/W
			[2]	-	150	175	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



FR4 PCB, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

Table 1.	Cital acteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.5	-0.9	-1.3	V
I _{DSS}	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-2	μΑ
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-2	μΑ
		$V_{GS} = 4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-0.5	μΑ
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-0.5	μΑ
R _{DSon}	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -400 \text{ mA}; T_j = 25 \text{ °C}$	-	0.67	0.85	Ω
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -400 \text{ mA}; T_j = 150 \text{ °C}$	-	1.1	1.4	Ω
		V_{GS} = -2.5 V; I_{D} = -200 mA; T_{j} = 25 °C	-	1.2	1.5	Ω
		$V_{GS} = -1.8 \text{ V}; I_D = -10 \text{ mA}; T_j = 25 \text{ °C}$	-	1.8	2.8	Ω
9 _{fs}	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -200 \text{ mA}; T_j = 25 \text{ °C}$	-	610	-	mS
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -400 \text{ mA};$	-	0.76	1.14	nC
Q _{GS}	gate-source charge	$V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$	-	0.28	-	nC
Q_{GD}	gate-drain charge		-	0.18	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V; } f = 1 \text{ MHz; } V_{GS} = 0 \text{ V;}$	-	58	87	pF
C _{oss}	output capacitance	T _j = 25 °C	-	21	-	pF
C _{rss}	reverse transfer capacitance		-	12	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; R_L = 250 Ω ; V_{GS} = -4.5 V;	-	18	36	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	30	-	ns
t _{d(off)}	turn-off delay time		-	80	160	ns
t _f	fall time		-	72	-	ns
Source-di	ain diode					
V_{SD}	source-drain voltage	$I_S = -300 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-0.48	-0.84	-1.2	V

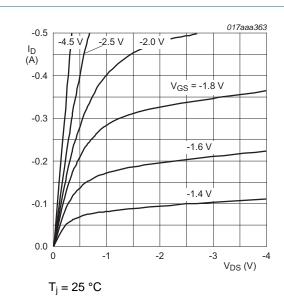
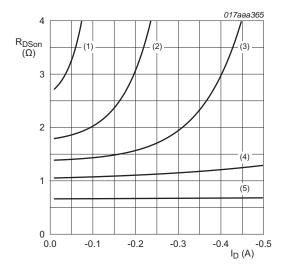


Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C$

(1) $V_{GS} = -1.5 \text{ V}$

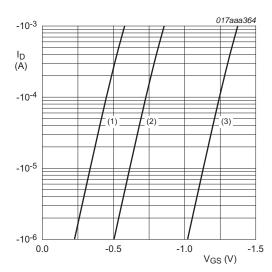
(2) $V_{GS} = -1.8 \text{ V}$

(3) $V_{GS} = -2.0 \text{ V}$

(4) $V_{GS} = -2.5 \text{ V}$

(5) $V_{GS} = -4.5 \text{ V}$

Fig 9. Drain-source on-state resistance as a function of drain current; typical values



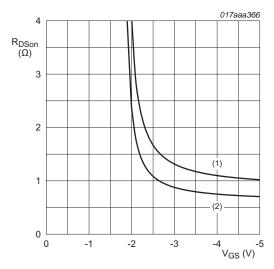
 $T_i = 25 \,^{\circ}\text{C}; \, V_{DS} = -5 \,^{\circ}\text{V}$

(1) minimum values

(2) typical values

(3) maximum values

Fig 8. Sub-threshold drain current as a function of gate-source voltage

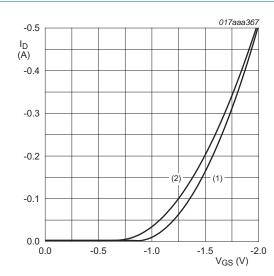


 $I_D = -400 \text{ mA}$

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_j = 25 \, ^{\circ}\text{C}$

Fig 10. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_j = 25 \, ^{\circ}C$$

(2)
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

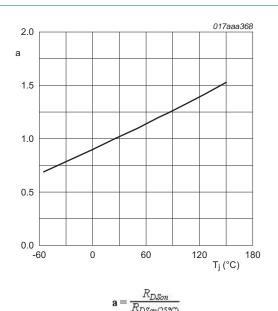
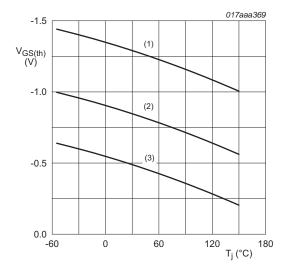


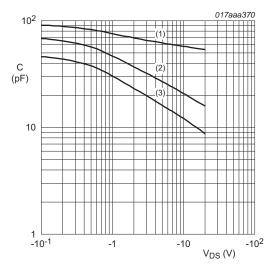
Fig 12. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 I_D = -0.25 mA; V_{DS} = V_{GS}

- (1) maximum values
- (2) typical values
- (3) minimum values

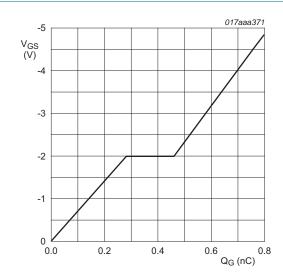
Fig 13. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $I_D = -0.4 \text{ A}; V_{DD} = -10 \text{ V}; T_{amb} = 25 \text{ °C}$

Fig 15. Gate-source voltage as a function of gate charge; typical values

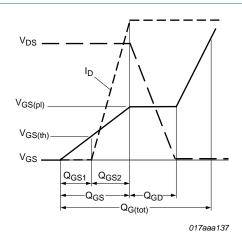
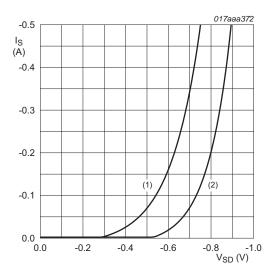


Fig 16. Gate charge waveform definitions



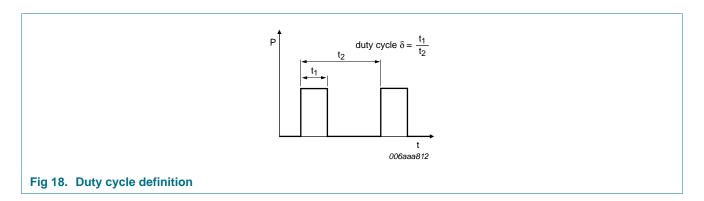
 $V_{GS} = 0 V$

(1) $T_{amb} = 150 \, ^{\circ}C$

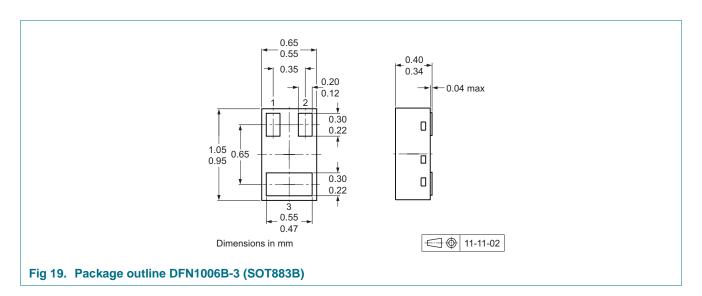
(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 17. Source current as a function of source-drain voltage; typical values

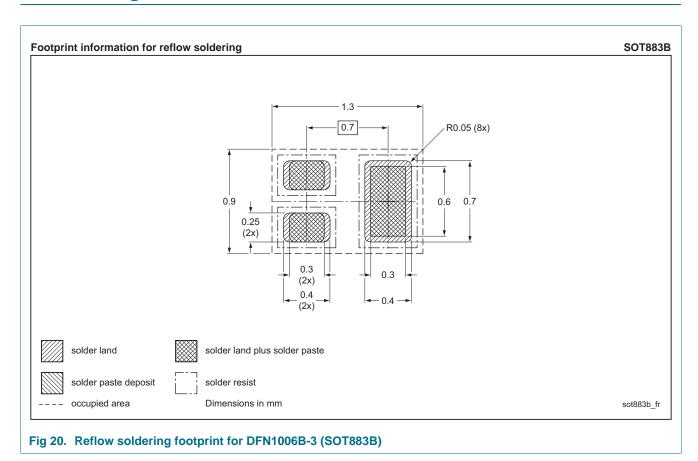
8. Test information



9. Package outline



10. Soldering





11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMZB670UPE v.3	20120323	Product data sheet	-	PMZB670UPE v.2
Modifications:	• 1.2 "Features	and benefits" is corrected.		
PMZB670UPE v.2	20120207	Product data sheet	-	PMZB670UPE v.1
PMZB670UPE v.1	20120131	Product data sheet	-	-

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Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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20 V, single P-channel Trench MOSFET

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